NSN 5962-01-369-6197

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Maximum Power Dissipation Rating:
1.1 watts
Operating Tempurature Range:
-55.0/+125.0 degrees celsius
Storage Tempurature Range:
-65.0/+150.0 degrees celsius
End Application:
An/fps-124 (ssradar)
Features Provided:
Programmed
Inclosure Material:
Ceramic
Inclosure Configuration:
Dual-in-line
Output Logic Form:
Bipolar metal-oxide semiconductor
Input Circuit Pattern:
16 input
Case Outline Source And Designator:
D-8 mil-m-38510
Current Rating Per Characteristic:
100.00 milliamperes reverse current, dc
Terminal Surface Treatment:
Solder
Product Name:
Microcircuit, digital bipolar, programmable logic, monolithic silicon
Voltage Rating And Type Per Characteristic:
-0.5 volts total supply and 12.0 volts total supply and 4.5 volts positive power supply span and 5.5 volts positive power supply span
Memory Device Type:
Pal
Hybrid Technology Type:
Monolithic

Test Data Document:

81349-mil-m-38510 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.). And 96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).

Terminal Type And Quantity:

20 printed circuit

Specification Data:

56232-1212249 manufacturers specification control

Specification Or Standard:

218 number

Departure From Cited Document:

Altered by programming marking & testing

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Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

Yes - demil/mli

Fiig:

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